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650 V Power SiC Merged PIN Schottky Diode, 6 A



PRIMARY CHARACTERISTICS					
I _{F(AV)}	6 A				
V _R	650 V				
V _F at I _F at 150 °C	1.70 V				
T _J max.	175 °C				
I _R at V _R at 175 °C	4.4 µA				
Q _C (V _R = 400 V)	17 nC				
Package	2L TO-220AC				
Circuit configuration	Single				

FEATURES

 Majority carrier diode using Schottky technology on SiC wide band gap material RoHS



HALOGEN

FREE

- Positive V_F temperature coefficient for easy COMPLIANT paralleling
- Virtually no recovery tail and no switching losses
- Temperature invariant switching behavior
- 175 °C maximum operating junction temperature
- MPS structure for high ruggedness to forward current surge events
- Meets JESD 201 class 1A whisker test
- Solder bath temperature 275 °C maximum, 10 s per JESD 22-B106
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

Wide band gap SiC based 650 V Schottky diode, designed for high performance and ruggedness.

Optimum choice for high speed hard switching and efficient operation over a wide temperature range, it is also recommended for all applications suffering from Silicon ultrafast recovery behavior.

Typical applications include AC/DC PFC and DC/DC ultra high frequency output rectification in FBPS and LLC converters.

MECHANICAL DATA

Case: 2L TO-220AC

Molding compound meets UL 94 V-0 flammability rating Base P/N-M3 - halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

Mounting torque: 10 in-lbs maximum

ABSOLUTE MAXIMUM RATINGS ($T_A = 25 \text{ °C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	V _{RRM}		650	V		
Average rectified forward current	I _{F(AV)}	T _C = 127 °C (DC)	6	A		
DC blocking voltage	V _{DC}		650	V		
Repetitive peak surge current	I _{FRM}	T_C = 25 °C, f = 50 Hz, square wave, DC = 25 %	23			
Non-repetitive peak forward surge current	I _{FSM}	T_{C} = 25 °C, t_{p} = 10 ms, half sine wave	39	А		
Non-repetitive peak forward surge current		T_{C} = 110 °C, t_{p} = 10 ms, half sine wave	37	L		
Power dissipation Ptot		T _C = 25 °C	42	W		
Power dissipation	P _{tot} ⁽¹⁾	T _C = 110 °C	18	~~		
124	∫i ² dt	T _C = 25 °C	8	A2-		
l ² t value		T _C = 110 °C	6.8	A ² s		
Operating junction and storage temperatures	T _J ⁽²⁾ , T _{Stg}		-55 to +175	°C		

Notes

⁽¹⁾ Based on maximum R_{th}

 $^{(2)}$ The heat generated must be less than the thermal conductivity from junction-to-ambient: dP_D/dT_J < 1/R_{0JA}

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ELECTRICAL SPECIFICATIONS ($T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
		I _F = 6 A	-	1.45	1.70		
Forward voltage	V _F	I _F = 6 A, T _J = 150 °C	-	1.70	2.10	V	
		I _F = 6 A, T _J = 175 °C	-	1.80	-		
		V _R = V _R rated	-	-	35		
Reverse leakage current	I _R	$V_R = V_R$ rated, $T_J = 150 \ ^\circ C$	-	-	75	μA	
		$V_{R} = V_{R}$ rated, $T_{J} = 175 \text{ °C}$	-	4.4	-		
Total capacitance	С	V _R = 1 V, f = 1 MHz	-	250	-	рF	
	C	V _R = 400 V, f = 1 MHz	-	27	-		
Total capacitive charge	Q _C	V _R = 400 V, f = 1 MHz	-	17	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS (T _A = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Thermal resistance, junction-to-case	R _{thJC}		-	2.55	3.6	°C/W	
Marking device				C06E	T07T		

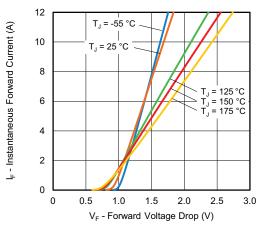


Fig. 1 - Typical Forward Voltage Drop Characteristics

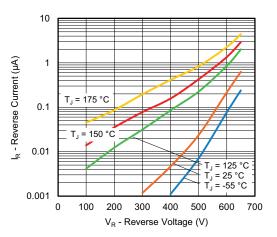


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

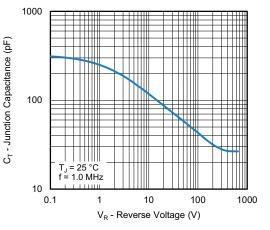


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

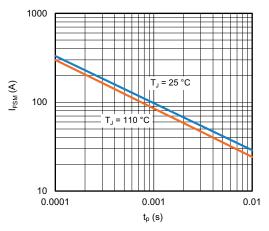
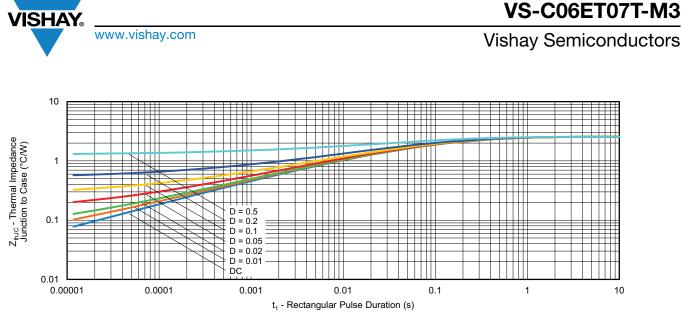
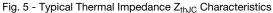


Fig. 4 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration (Square Wave)

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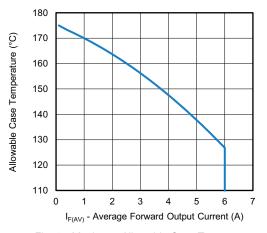


Fig. 6 - Maximum Allowable Case Temperature vs. Average Forward Current

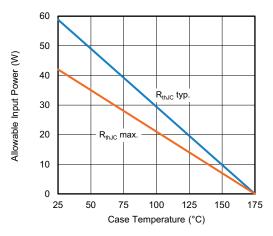


Fig. 7 - Forward Power Loss Characteristics

7 6 Capacitive Energy (µJ) 5 4 3 2 T_J = 25 °C, 1.0 MHz 1 C V dV $E_I =$ 0 0 100 200 300 400 500 600 700 Reverse Voltage (V)

Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage

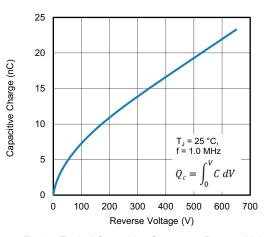


Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage

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Device code	VS-	С	06	Е	т	07	т	-M3
	1	2	3	4	5	6	7	8
	1	- Visl	nay Sem	niconduo	ctors pr	oduct		
	2	- C =	SiC dio	de				
	3	- Cur	rent rati	ng (06 =	= 6 A)			
	4	- E=	single c	liode				
	5	- Pac	kage T	D-220				
	6	- Vol	tage rati	ng: (07 :	= 650 V)		
	7	- T=	true 2 p	in				
	8	- Env	ironmer	ntal digit				
		-M3	3 = halog	gen-free	, RoHS	-compli	ant, and	d termir

ORDERING INFORMATION						
PREFERRED P/N	BASE QUANTITY	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-C06ET07T-M3	50/tube	1000	Antistatic plastic tubes			

LINKS TO RELATED DOCUMENTS				
Dimensions www.vishay.com/doc?96069				
Part marking information	www.vishay.com/doc?95391			



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